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U.S. Patent Documents									
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)									
	AR "Design of New Structural High Breakdown Voltage V-MOSFETStatic Shield V-MOSFET", Kuniharu Katoh and Yuuki Shimada, Electronics and Communications in Japan, Vol. 66-C, No. 6, 1983, pp. 95-105.								
AS "U-MOS Power FET", Daisuke Ueda, Hiromitsu, Takagi, Kazuyoshi Kitamura, Goryo Hagio and Masaru Nahara, National Technical Report, Vol. 29, No. 2, April, 1983, pp. 143-150.									
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